

## Diode – Diode Module

### Features

- Improved glass passivation for high reliability
- Exceptional stability at high temperatures
- High di/dt and dv/dt capabilities
- Low thermal resistance

### Maximum Ratings ( $T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Values	Units
Maximum average forward current @ $T_J = 85^{\circ}\text{C}$	$I_{F(AV)}$	56	A
Maximum average RMS forward current	$I_{F(RMS)}$	88	A
Maximum non-repetitive surge current @ $t = 10\text{ms}$	$I_{FSM}$	1300	A
Maximum $I^2t$ for fusing @ $t = 10\text{ms}$	$I^2t$	12.5	$\text{kA}^2\text{s}$



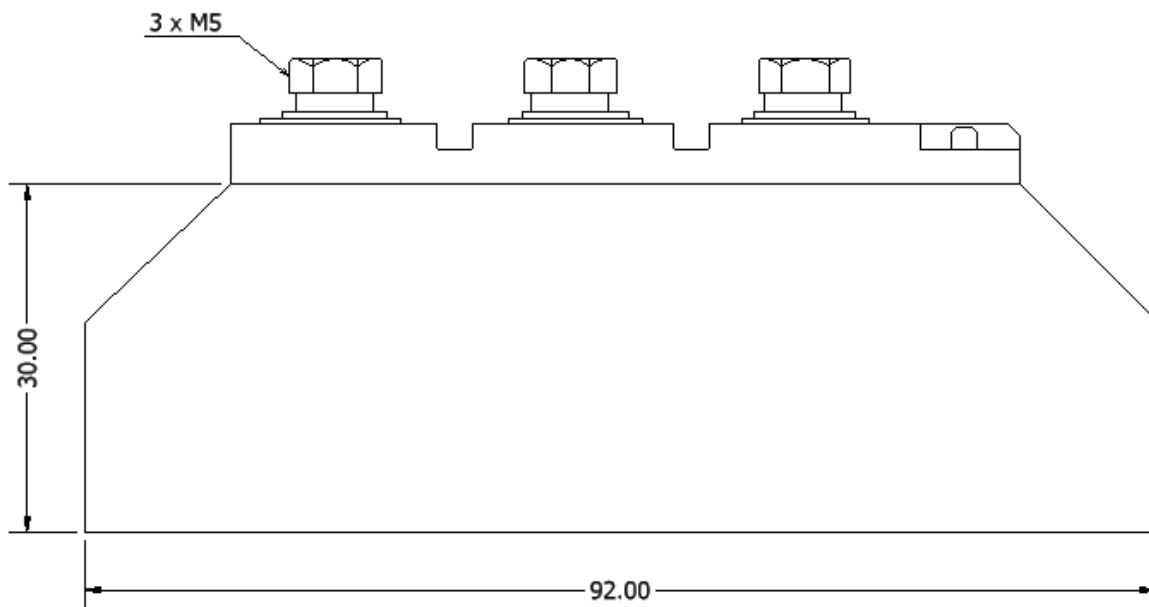
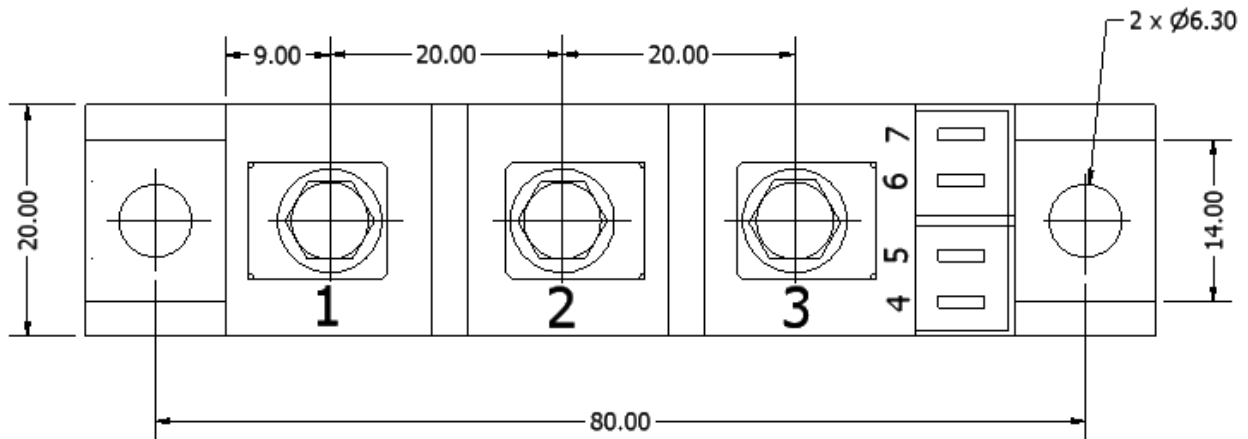
**M1 PACKAGE**

### Thermal & Mechanical Specifications ( $T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Values	Units
Operating junction temperature range	$T_J$	-65 to +125	$^{\circ}\text{C}$
Thermal resistance, junction to case	$R_{th(JC)}$	0.8	$^{\circ}\text{C}/\text{W}$

### Electrical Characteristics ( $T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Values	Units
Maximum average on-state current, $180^{\circ}\text{C}$ sinusoidal	$I_{T(max)}$	56	A
Maximum repetitive peak reverse voltage range	$V_{RRM}$	200 to 1600	V
Forward voltage drop	$V_{FM}$	1.4	V
RMS isolation voltage	$V_{ISO}$	2500	V



ALL DIMENSIONS ARE IN MM

**Diode Configuration**

